
2SD2300

Silicon NPN Triple Diffused

HITACHI

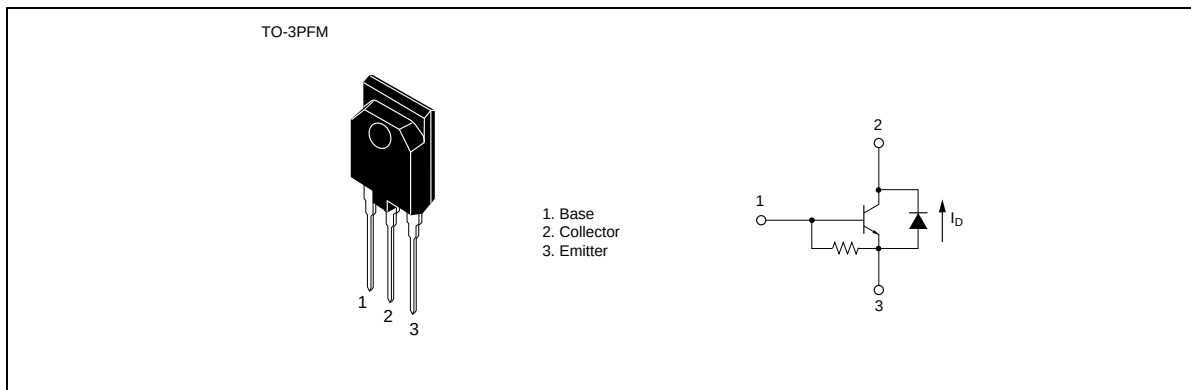
Application

CTV horizontal deflection output

Features

- High breakdown voltage
 $V_{CBO} = 1500 \text{ V}$
- Built-in damper diode type

Outline



2SD2300

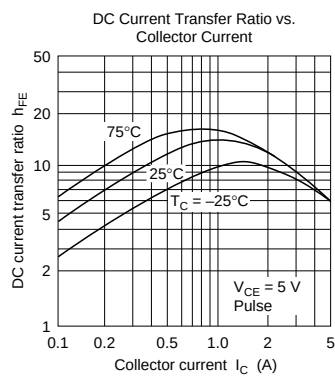
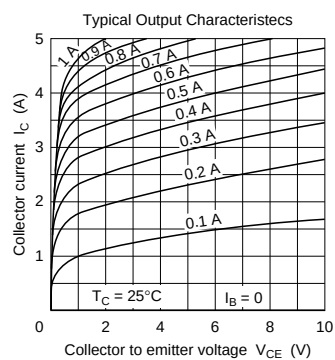
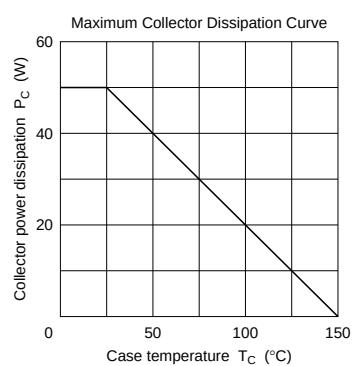
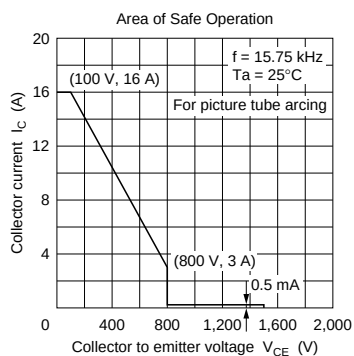
Absolute Maximum Ratings (Ta = 25°C)

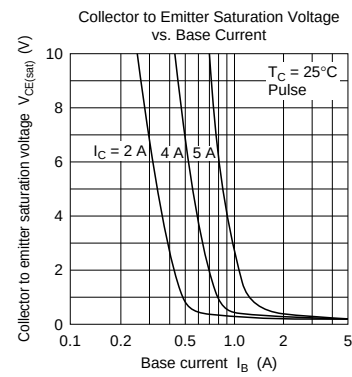
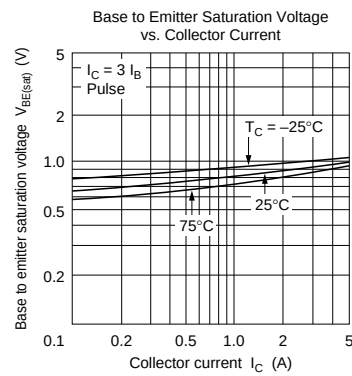
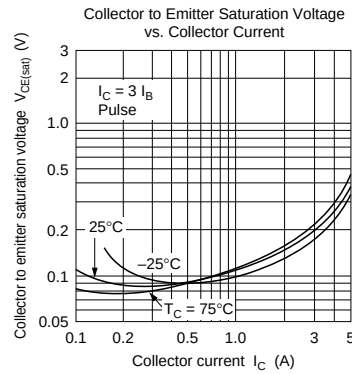
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	1500	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	5	A
Collector peak current	$I_{C(peak)}$	6	A
Collector surge current	$I_{C(surge)}$	16	A
Collector power dissipation	P_C^{*1}	50	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C
C to E diode forward current	I_D	6	A

Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 350\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{ V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE}	—	—	20		$V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 4.5\text{ A}$, $I_B = 1.2\text{ A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 4.5\text{ A}$, $I_B = 1.2\text{ A}$
C to E diode forward voltage	V_{ECF}	—	—	3.0	V	$I_F = 6\text{ A}$
Fall time	t_f	—	—	1.0	μs	$I_{CP} = 4\text{ A}$, $I_{B1} = 0.8\text{ A}$, $I_{B2} \approx -1.5\text{ A}$





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